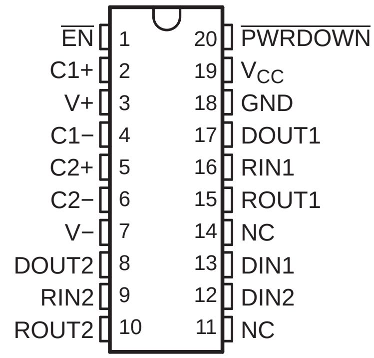
FEATURES

- **ESD Protection for RS-232 Bus Pins**
  - **±15-kV Human-Body Model (HBM)**
  - **±8-kV IEC 61000-4-2, Contact Discharge**
  - **±15-kV IEC 61000-4-2, Air-Gap Discharge**
- **Meet or Exceed the Requirements of TIA/EIA-232-F and ITU v.28 Standards**
- **Operate With 3-V to 5.5-V V_{CC} Supply**
- **Operate up to 1000 kbit/s**
- **Two Drivers and Two Receivers**
- **Low Standby Current . . . 1 μA Typ**
- **External Capacitors . . . 4 × 0.1 μF**
- **Accepts 5-V Logic Input With 3.3-V Supply**

APPLICATIONS

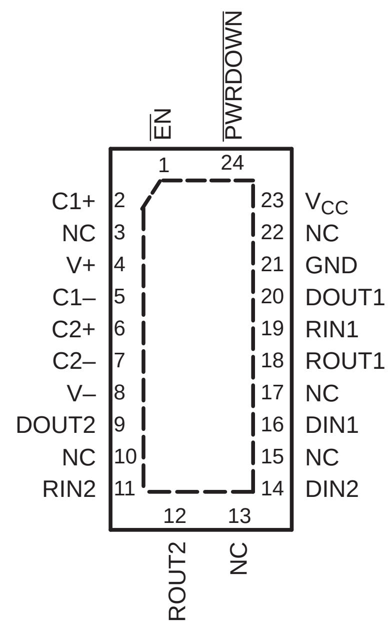
- **Battery-Powered Systems**
- **PDAs**
- **Notebooks**
- **Laptops**
- **Palmtop PCs**
- **Hand-Held Equipment**

DB, DW, OR PW PACKAGE (TOP VIEW)



NC − No internal connection

RHL PACKAGE (TOP VIEW)



NC − No internal connection

DESCRIPTION/ ORDERING INFORMATION

The SN65C3222E and SN75C3222E consist of two line drivers, two line receivers, and a dual charge-pump circuit with ±15-kV ESD protection pin to pin (serial-port connection pins, including GND).

The devices meet the requirements of TIA/EIA-232-F and provide the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 3-V to 5.5-V supply. The devices operate at typical data signaling rates up to 1000 kbit/s and are improved drop-in replacements for industry-popular '3222 two-driver, two-receiver functions.

The SN65C3222E and SN75C3222E can be placed in the power-down mode by setting the power-down ($\overline{\text{PWRDOWN}}$) input low, which draws only 1 μA from the power supply. When the devices are powered down, the receivers remain active while the drivers are placed in the high-impedance state. Also, during power down, the onboard charge pump is disabled; V+ is lowered to V_{CC}, and V– is raised toward GND. Receiver outputs also can be placed in the high-impedance state by setting enable ($\overline{\text{EN}}$) high.

ORDERING INFORMATION

T_A	PACKAGE(1)		ORDERABLE PART NUMBER	TOP-SIDE MARKING
0°C to 70°C	SOIC – DW	Tube of 25	SN75C3222EDW	75C3222E
		Reel of 2000	SN75C3222EDWR	
	SSOP – DB	Tube of 70	SN75C3222EDB	MY222E
		Reel of 2000	SN75C3222EDBR	
	TSSOP – PW	Tube of 70	SN75C3222EPW	MY222E
		Reel of 2000	SN75C3222EPWR	
–40°C to 85°C	SOIC – DW	Tube of 25	SN65C3222EDW	65C3222E
		Reel of 2000	SN65C3222EDWR	
	SSOP – DB	Tube of 70	SN65C3222EDB	MU222E
		Reel of 2000	SN65C3222EDBR	
	TSSOP – PW	Tube of 70	SN65C3222EPW	MU222E
		Reel of 2000	SN65C3222EPWR	

(1) Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

FUNCTION TABLES

Each Driver(1)

INPUTS		OUTPUT
DIN	$\overline{\text{PWRDOWN}}$	DOUT
X	L	Z
L	H	H
H	H	L

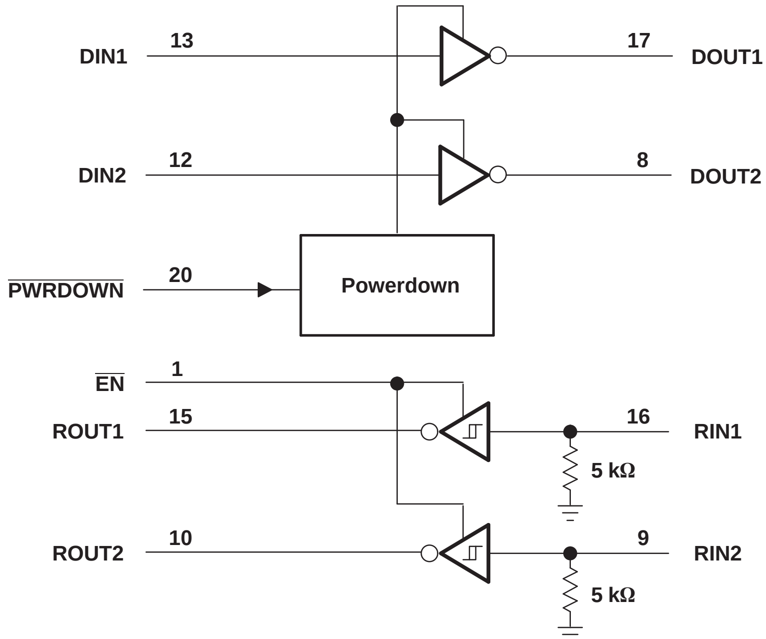
(1) H = high level, L = low level, X = irrelevant, Z = high impedance

Each Receiver(1)

INPUTS		OUTPUT
RIN	$\overline{\text{EN}}$	ROUT
L	L	H
H	L	L
X	H	Z
Open	L	H

(1) H = high level, L = low level, X = irrelevant,
Z = high impedance (off),
Open = input disconnected or connected driver off

LOGIC DIAGRAM (POSITIVE LOGIC)



Pin numbers are for the DB, DW, and PW packages.

Absolute Maximum Ratings(1)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_{CC}	Supply voltage range(2)		–0.3	6	V
V+	Positive-output supply voltage range(2)		–0.3	7	V
V–	Negative-output supply voltage range(2)		0.3	–7	V
V+ – V–	Supply voltage difference(2)			13	V
V_I	Input voltage range	Driver ($\overline{EN}$, $\overline{PWRDOWN}$)	–0.3	6	V
		Receiver	–25	25	
V_O	Output voltage range	Driver	–13.2	13.2	V
		Receiver	–0.3	V_{CC} + 0.3	
θ_{JA}	Package thermal impedance(3)(4)	DB package		70	°C/W
		DW package		58	
		PW package		83	
		RHL package		TBD	
T_J	Operating virtual junction temperature			150	°C
T_{stg}	Storage temperature range		–65	150	°C

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltages are with respect to network GND.
(3) Maximum power dissipation is a function of T_J(max), θ_{JA}, and T_A. The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_J(max) – T_A)/\theta_{JA}$. Operating at the absolute maximum T_J of 150°C can affect reliability.
(4) The package thermal impedance is calculated in accordance with JESD 51-7.

Recommended Operating Conditions(1)

See Figure 5

				MIN	NOM	MAX	UNIT
	Supply voltage		V_{CC} = 3.3 V	3	3.3	3.6	V
			V_{CC} = 5 V	4.5	5	5.5	
V_{IH}	Driver and control high-level input voltage	DIN, $\overline{\text{EN}}$, $\overline{\text{PWRDOWN}}$	V_{CC} = 3.3 V	2			V
			V_{CC} = 5 V	2.4			
V_{IL}	Driver and control low-level input voltage	DIN, $\overline{\text{EN}}$, $\overline{\text{PWRDOWN}}$				0.8	V
V_I	Driver and control input voltage	DIN, $\overline{\text{EN}}$, $\overline{\text{PWRDOWN}}$		0		5.5	V
V_I	Receiver input voltage			–25		25	V
T_A	Operating free-air temperature		SN75C3222E	0		70	°C
			SN65C3222E	–40		85	

(1) Test conditions are C1–C4 = 0.1 μF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μF, C2–C4 = 0.33 μF at V_{CC} = 5 V ± 0.5 V.

Electrical Characteristics(1)

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5)

PARAMETER		TEST CONDITIONS	MIN	TYP(2)	MAX	UNIT
I_I	Input leakage current ($\overline{\text{EN}}$, $\overline{\text{PWRDOWN}}$)			±0.01	±1	μA
I_{CC}	Supply current	No load, $\overline{\text{PWRDOWN}}$ at V_{CC}		0.3	1	mA
	Supply current (powered off)	No load, $\overline{\text{PWRDOWN}}$ at GND		1	10	μA

(1) Test conditions are C1–C4 = 0.1 μF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μF, C2–C4 = 0.33 μF at V_{CC} = 5 V ± 0.5 V.
(2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

DRIVER SECTION

Electrical Characteristics[1]

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5)

PARAMETER		TEST CONDITIONS		MIN	TYP[2]	MAX	UNIT
V_{OH}	High-level output voltage	DOUT at R_L = 3 kΩ to GND,	DIN = GND	5	5.4		V
V_{OL}	Low-level output voltage	DOUT at R_L = 3 kΩ to GND,	DIN = V_{CC}	–5	–5.4		V
I_{IH}	High-level input current	V_I = V_{CC}			±0.01	±1	µA
I_{IL}	Low-level input current	V_I at GND			±0.01	±1	µA
I_{OS}	Short-circuit output current[3]	V_{CC} = 3.6 V V_{CC} = 5.5 V	V_O = 0 V		±35	±60	mA
r_o	Output resistance	V_{CC}, V+, and V– = 0 V,	V_O = ±2 V	300	10M		Ω
I_{OZ}	Output leakage current	$\overline{\text{PWRDOWN}}$ = GND	V_{CC} = 3 V to 3.6 V, V_O = ±12 V			±25	µA
			V_{CC} = 4.5 V to 5.5 V, V_O = ±10 V			±25	

(1) Test conditions are C1–C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2–C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.
(2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
(3) Short-circuit durations should be controlled to prevent exceeding the device absolute power dissipation ratings, and not more than one output should be shorted at a time.

Switching Characteristics[1]

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5)

PARAMETER		TEST CONDITIONS			MIN	TYP[2]	MAX	UNIT
	Maximum data rate (See Figure 1)	R_L = 3 kΩ, One DOUT switching	C_L = 1000 pF		250			kbit/s
			C_L = 250 pF,	V_{CC} = 3 V to 4.5 V	1000			
			C_L = 1000 pF,	V_{CC} = 4.5 V to 5.5 V	1000			
$t_{sk(p)}$	Pulse skew[3]	C_L = 150 pF to 2500 pF,	R_L = 3 kΩ to 7 kΩ,	See Figure 2		300		ns
SR(tr)	Slew rate, transition region (see Figure 1)	R_L = 7 kΩ,	C_L = 150 pF to 1000 pF		8		90	V/µs
		R_L = 3 kΩ	C_L = 1000 pF		12		60	
			C_L = 150 pF to 250 pF		24		150	

(1) Test conditions are C1–C4 = 0.1 µF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 µF, C2–C4 = 0.33 µF at V_{CC} = 5 V ± 0.5 V.
(2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
(3) Pulse skew is defined as $|t_{PLH} – t_{PHL}|$ of each channel of the same device.

RECEIVER SECTION

Electrical Characteristics[1]

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5)

PARAMETER		TEST CONDITIONS	MIN	TYP[2]	MAX	UNIT
V_{OH}	High-level output voltage	I_{OH} = –1 mA	V_{CC} – 0.6	V_{CC} – 0.1		V
V_{OL}	Low-level output voltage	I_{OL} = 1.6 mA			0.4	V
V_{IT+}	Positive-going input threshold voltage	V_{CC} = 3.3 V		1.5	2.4	V
		V_{CC} = 5 V		1.8	2.4	
V_{IT-}	Negative-going input threshold voltage	V_{CC} = 3.3 V	0.6	1.2		V
		V_{CC} = 5 V	0.8	1.5		
V_{hys}	Input hysteresis (V_{IT+} – V_{IT-})			0.3		V
I_{OZ}	Output leakage current	$\overline{EN}$ = 1		±0.05	±10	μA
r_i	Input resistance	V_I = ±3 V to ±25 V	3	5	7	kΩ

(1) Test conditions are C1–C4 = 0.1 μF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μF, C2–C4 = 0.33 μF at V_{CC} = 5 V ± 0.5 V.
(2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.

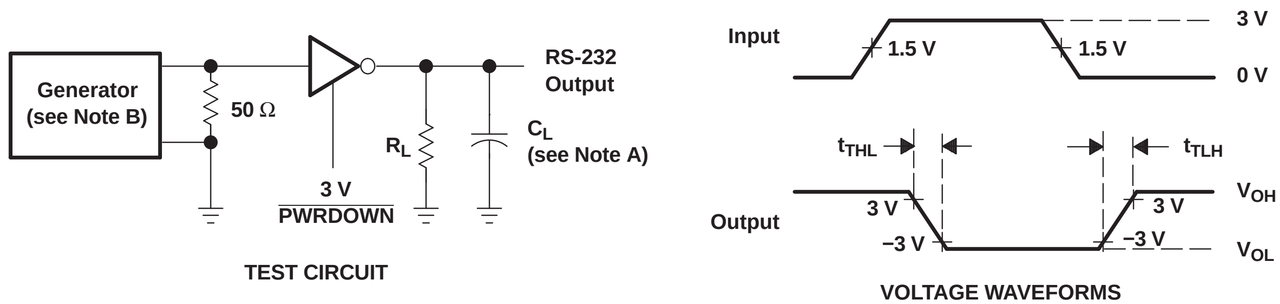
Switching Characteristics[1]

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS	TYP[2]	UNIT
t_{PLH}	Propagation delay time, low- to high-level output	C_L = 150 pF, See Figure 3	300	ns
t_{PHL}	Propagation delay time, high- to low-level output	C_L = 150 pF, See Figure 3	300	ns
t_{en}	Output enable time	C_L = 150 pF, R_L = 3 kΩ, See Figure 4	200	ns
t_{dis}	Output disable time	C_L = 150 pF, R_L = 3 kΩ, See Figure 4	200	ns
$t_{sk(p)}$	Pulse skew[3]	See Figure 3	300	ns

(1) Test conditions are C1–C4 = 0.1 μF at V_{CC} = 3.3 V ± 0.3 V; C1 = 0.047 μF, C2–C4 = 0.33 μF at V_{CC} = 5 V ± 0.5 V.
(2) All typical values are at V_{CC} = 3.3 V or V_{CC} = 5 V, and T_A = 25°C.
(3) Pulse skew is defined as $|t_{PLH} - t_{PHL}|$ of each channel of the same device.

PARAMETER MEASUREMENT INFORMATION

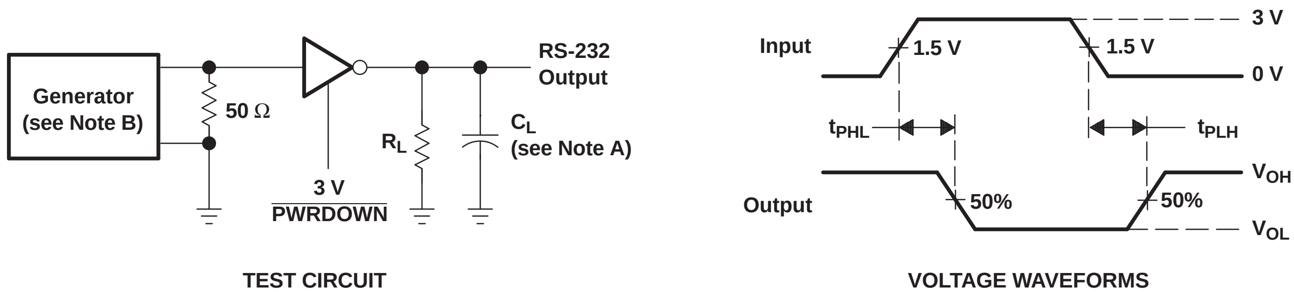


$$SR(tr) = \frac{6\ V}{t_{THL}\ or\ t_{TLH}}$$

A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 250 kbit/s, Z_O = 50 Ω, 50% duty cycle, $t_r \le 10$ ns, $t_f \le 10$ ns.

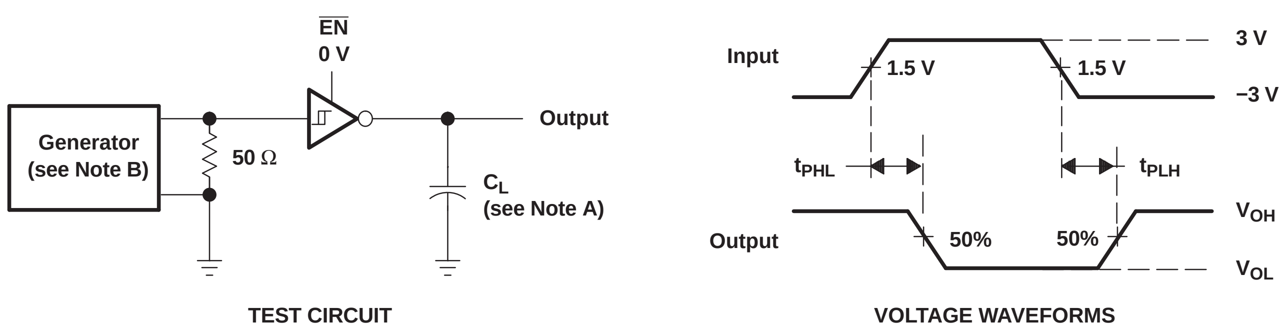
Figure 1. Driver Slew Rate



A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 250 kbit/s, Z_O = 50 Ω, 50% duty cycle, $t_r \le 10$ ns, $t_f \le 10$ ns.

Figure 2. Driver Pulse Skew

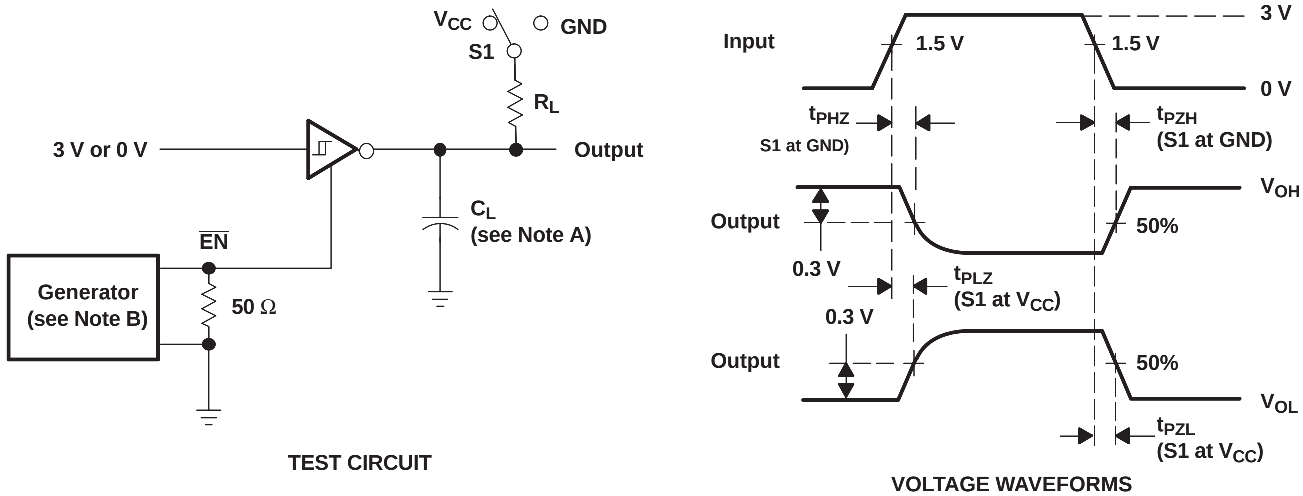


A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: Z_O = 50 Ω, 50% duty cycle, $t_r \le 10$ ns, $t_f \le 10$ ns.

Figure 3. Receiver Propagation Delay Times

PARAMETER MEASUREMENT INFORMATION (continued)

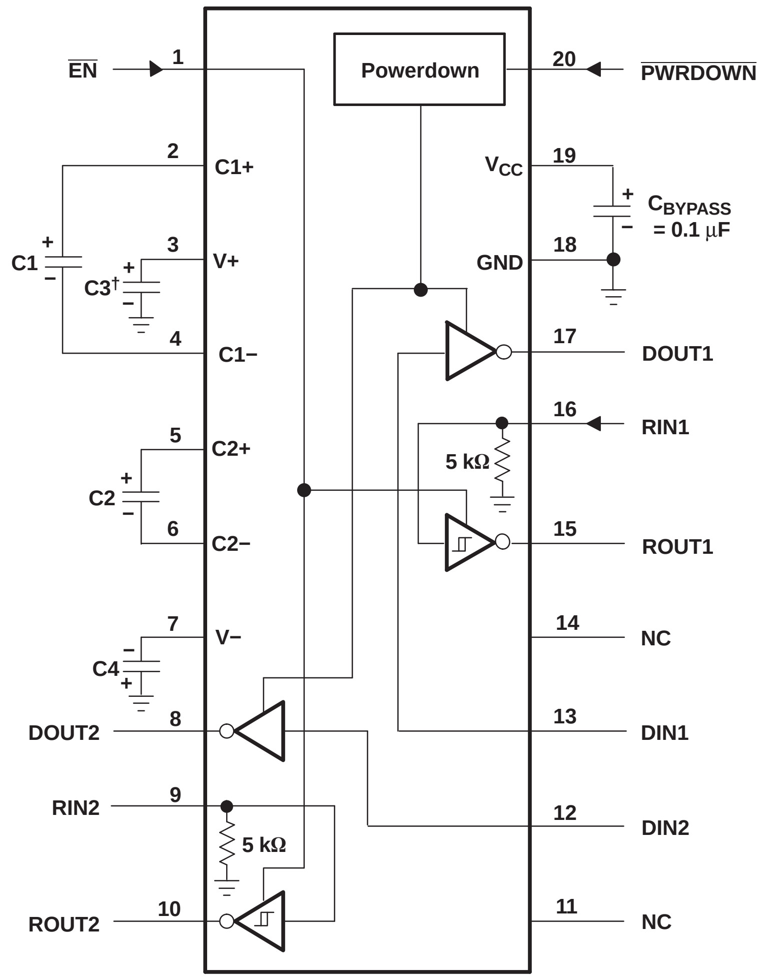


A. C_L includes probe and jig capacitance.

B. The pulse generator has the following characteristics: Z_O = 50 Ω, 50% duty cycle, $t_r \leq 10$ ns, $t_f \leq 10$ ns.

Figure 4. Receiver Enable and Disable Times

APPLICATION INFORMATION



† C3 can be connected to V_{CC} or GND.

NOTES: A. Resistor values shown are nominal.

B. NC − No internal connection

C. Nonpolarized ceramic capacitors are acceptable. If polarized tantalum or electrolytic capacitors are used, they should be connected as shown.

V_{CC} vs CAPACITOR VALUES

V_{CC}	C1	C2, C3, and C4
3.3 V ± 0.3 V	0.1 µF	0.1 µF
5 V ± 0.5 V	0.047 µF	0.33 µF
3 V to 5.5 V	0.1 µF	0.47 µF

Figure 5. Typical Operating Circuit and Capacitor Values

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN65C3222EDB	ACTIVE	SSOP	DB	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	MU222E	Samples
SN65C3222EDBG4	ACTIVE	SSOP	DB	20		TBD	Call TI	Call TI	-40 to 85		Samples
SN65C3222EDBR	ACTIVE	SSOP	DB	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	MU222E	Samples
SN65C3222EDBRG4	ACTIVE	SSOP	DB	20		TBD	Call TI	Call TI	-40 to 85		Samples
SN65C3222EDW	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3222E	Samples
SN65C3222EDWG4	ACTIVE	SOIC	DW	20		TBD	Call TI	Call TI	-40 to 85		Samples
SN65C3222EDWR	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	65C3222E	Samples
SN65C3222EDWRG4	ACTIVE	SOIC	DW	20		TBD	Call TI	Call TI	-40 to 85		Samples
SN65C3222EPW	ACTIVE	TSSOP	PW	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	MU222E	Samples
SN65C3222EPWG4	ACTIVE	TSSOP	PW	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	MU222E	Samples
SN65C3222EPWR	ACTIVE	TSSOP	PW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	MU222E	Samples
SN65C3222EPWRG4	ACTIVE	TSSOP	PW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	MU222E	Samples
SN75C3222EDBR	ACTIVE	SSOP	DB	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	MY222E	Samples
SN75C3222EPW	ACTIVE	TSSOP	PW	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	MY222E	Samples
SN75C3222EPWR	ACTIVE	TSSOP	PW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	0 to 70	MY222E	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

[2] Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

[3] MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

[4] There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

[5] Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

[6] Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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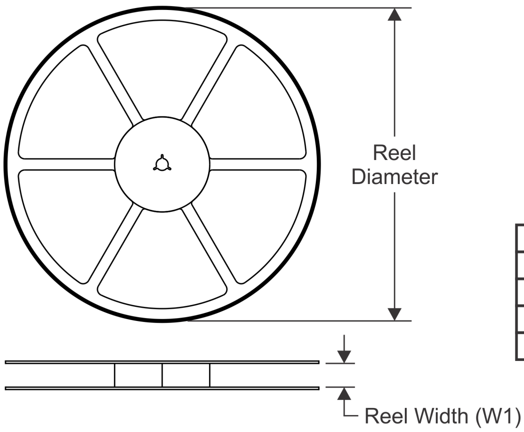
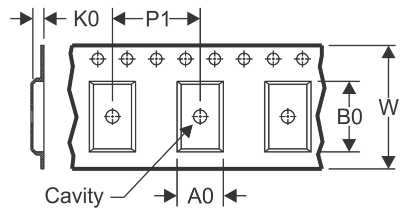
TAPE AND REEL INFORMATION

REEL DIMENSIONS

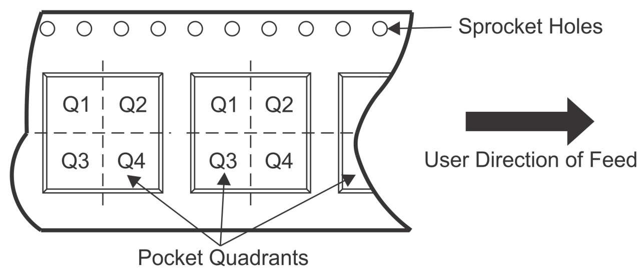


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

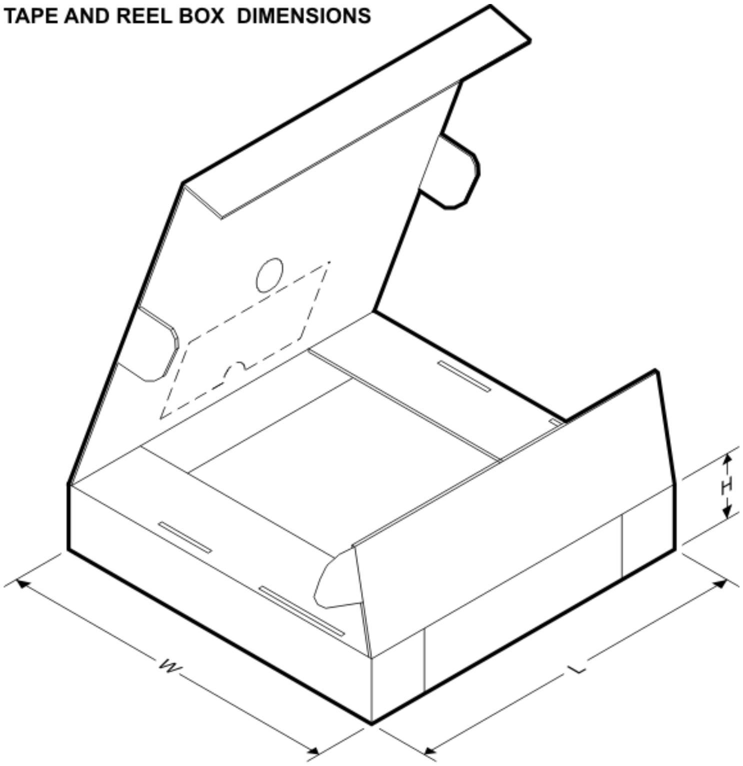
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65C3222EDBR	SSOP	DB	20	2000	330.0	16.4	8.2	7.5	2.5	12.0	16.0	Q1
SN65C3222EDWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
SN65C3222EPWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.1	1.6	8.0	16.0	Q1
SN75C3222EDBR	SSOP	DB	20	2000	330.0	16.4	8.2	7.5	2.5	12.0	16.0	Q1
SN75C3222EPWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.1	1.6	8.0	16.0	Q1

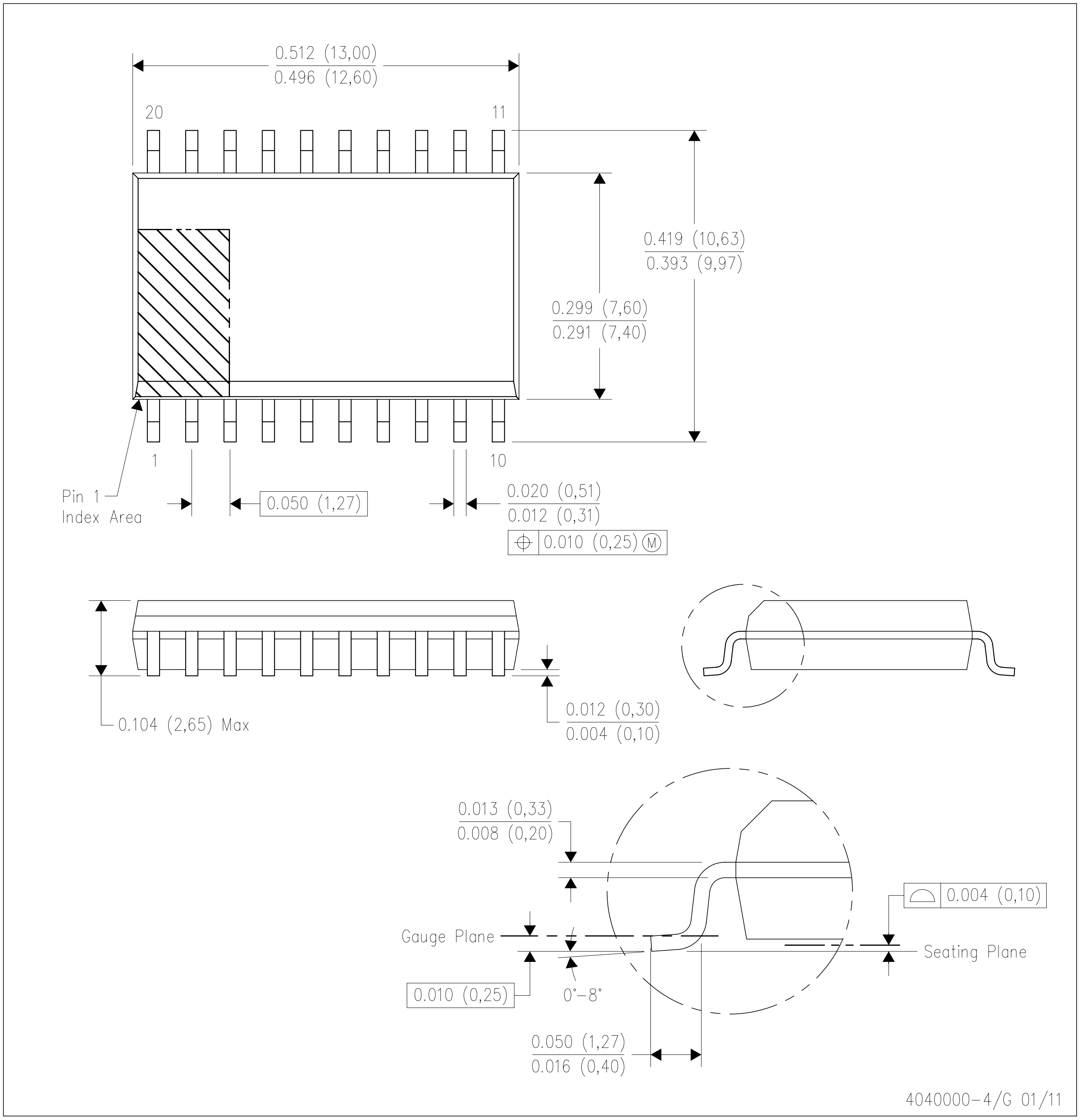
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

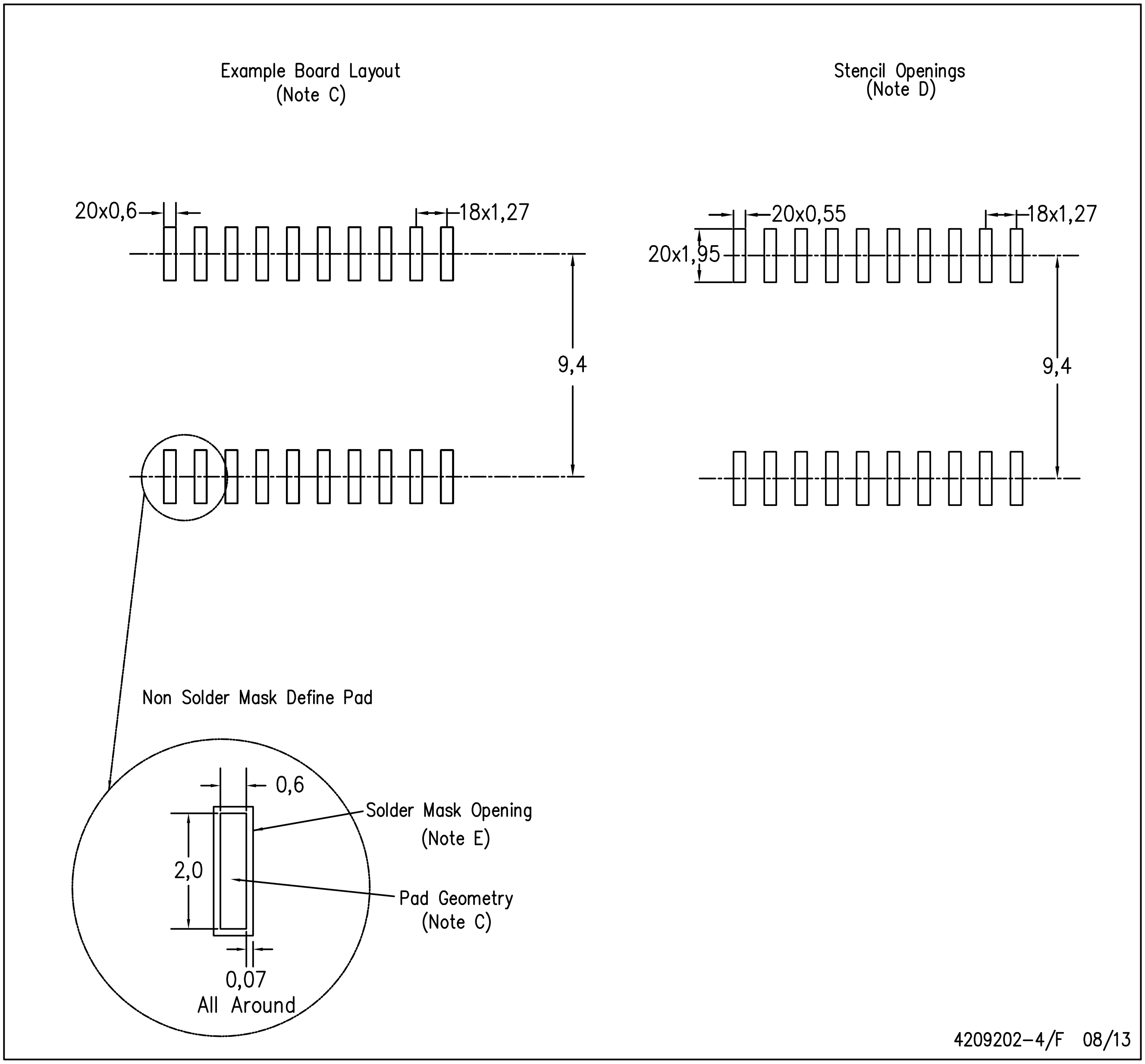
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN65C3222EDBR	SSOP	DB	20	2000	367.0	367.0	38.0
SN65C3222EDWR	SOIC	DW	20	2000	367.0	367.0	45.0
SN65C3222EPWR	TSSOP	PW	20	2000	367.0	367.0	38.0
SN75C3222EDBR	SSOP	DB	20	2000	367.0	367.0	38.0
SN75C3222EPWR	TSSOP	PW	20	2000	367.0	367.0	38.0

DW (R–PDSO–G20) PLASTIC SMALL OUTLINE



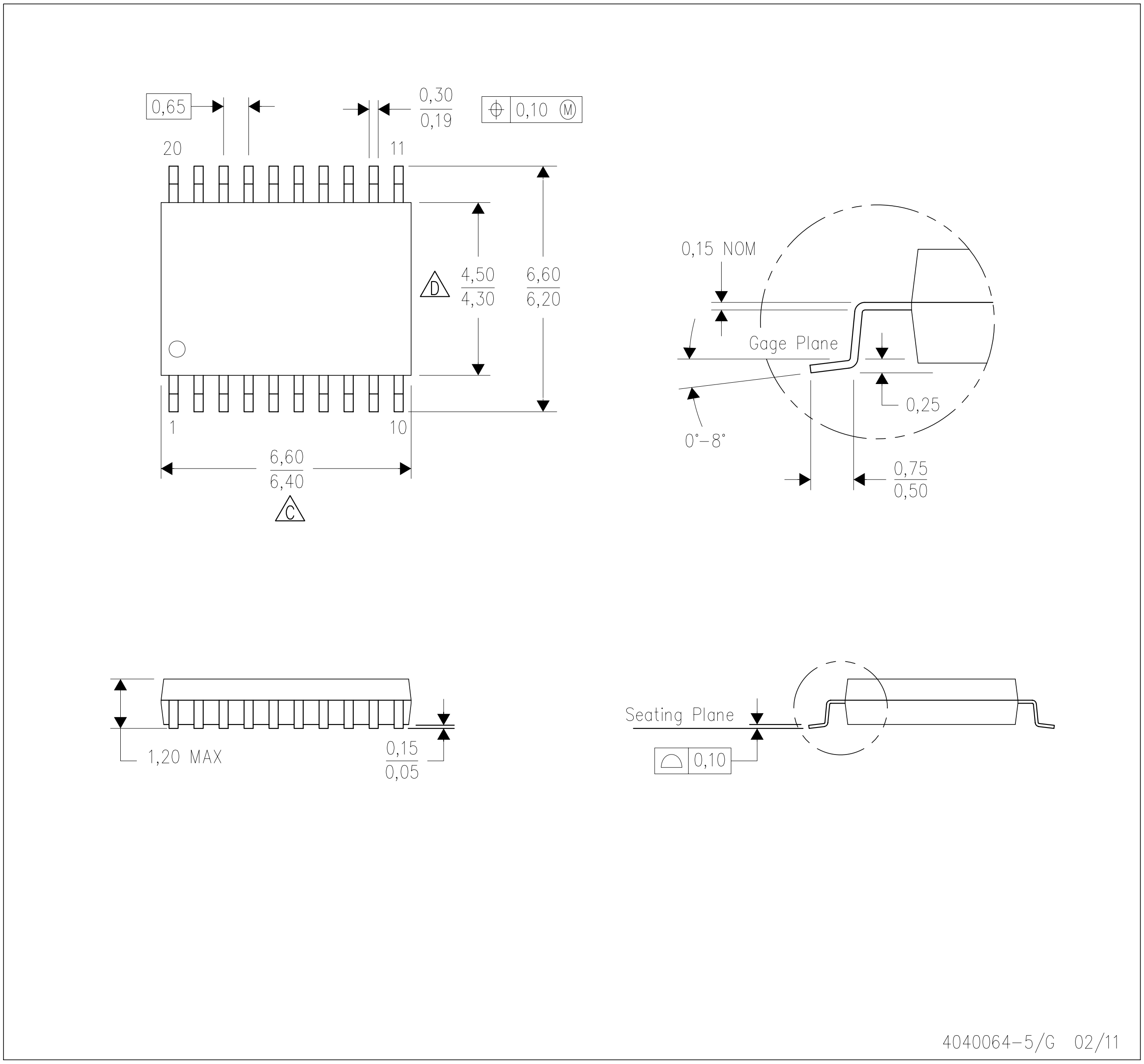
NOTES:
A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
D. Falls within JEDEC MS–013 variation AC.

DW (R–PDSO–G20) PLASTIC SMALL OUTLINE



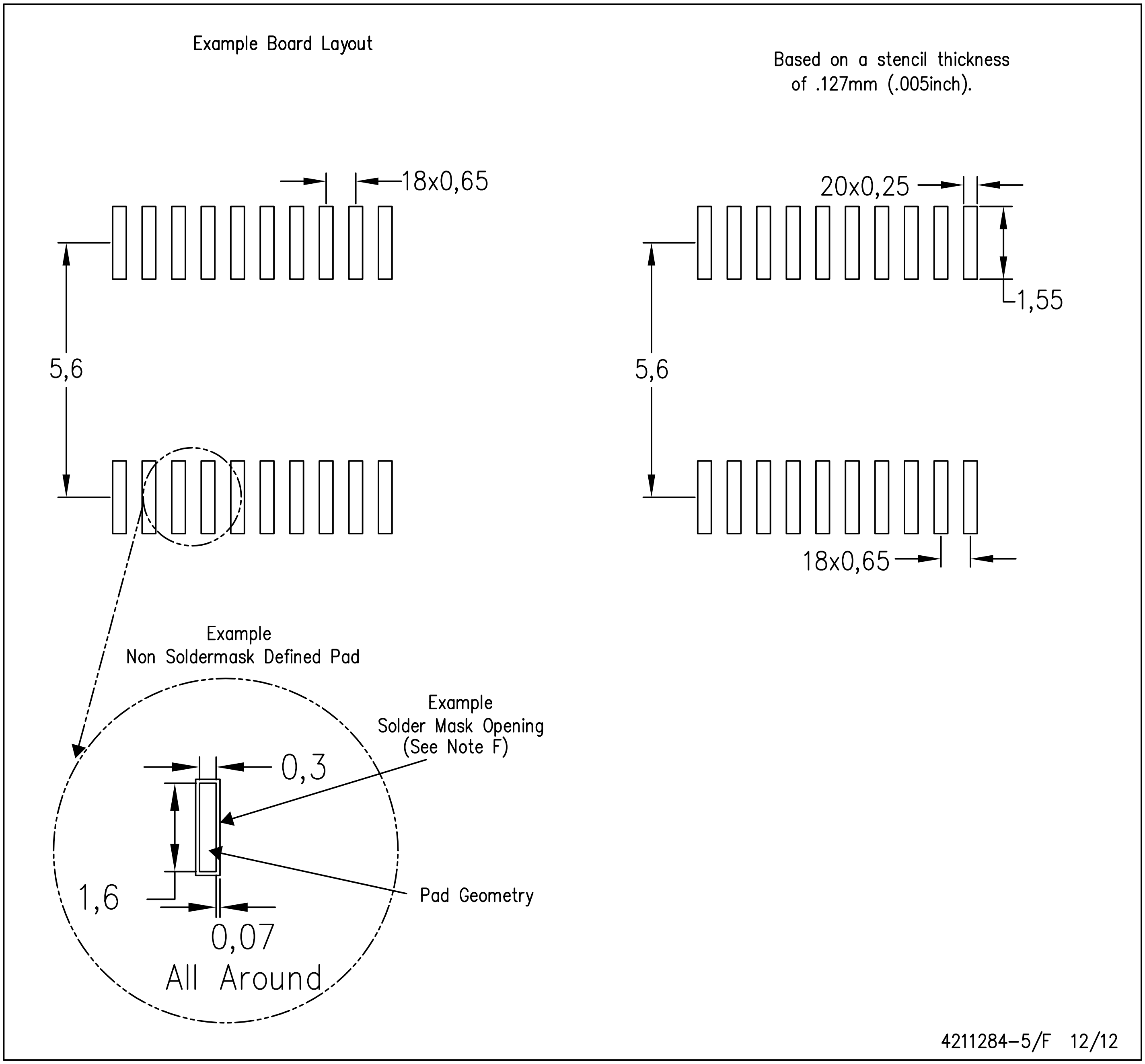
NOTES:
- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Refer to IPC7351 for alternate board design.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

PW (R–PDSO–G20) PLASTIC SMALL OUTLINE



NOTES: A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
E. Falls within JEDEC MO–153

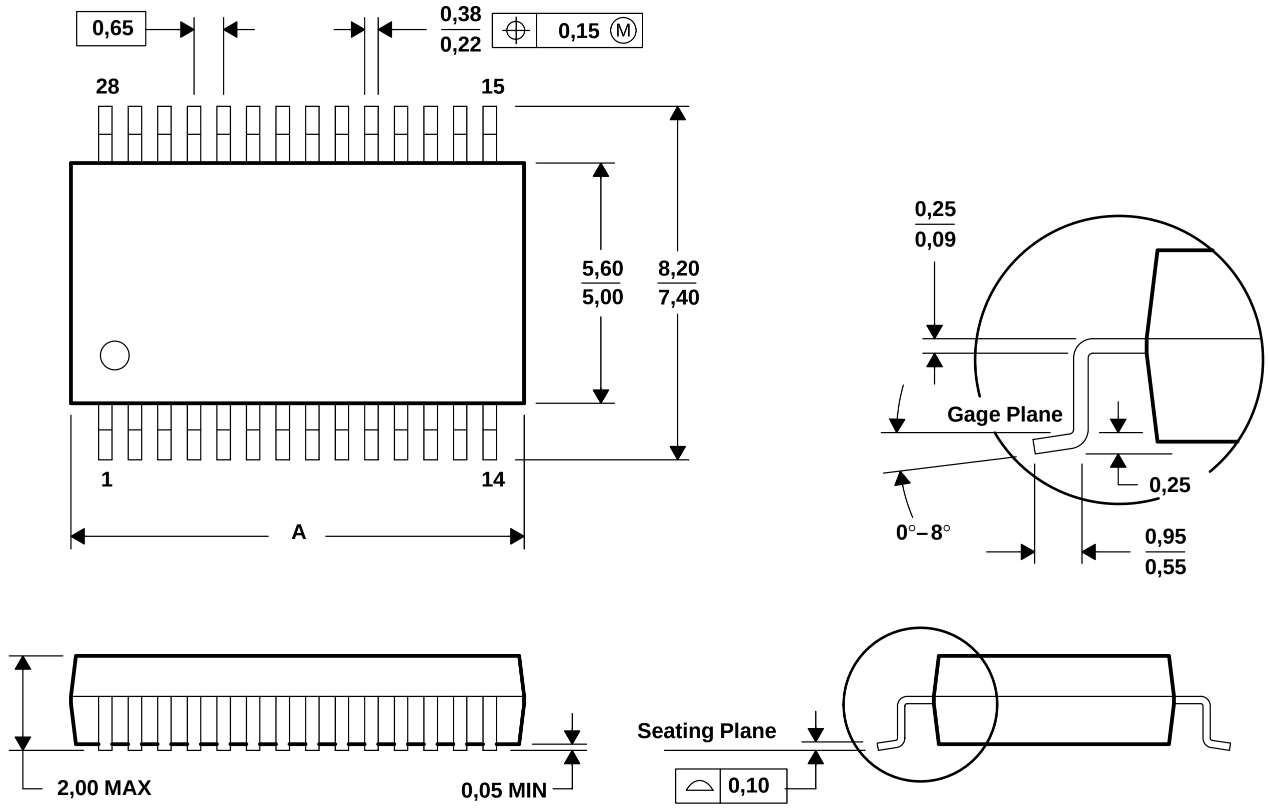
PW (R–PDSO–G20) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC–7351 is recommended for alternate design.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

DB (R-PDSO-G**) PLASTIC SMALL-OUTLINE

28 PINS SHOWN



PINS ** / DIM	14	16	20	24	28	30	38
A MAX	6,50	6,50	7,50	8,50	10,50	10,50	12,90
A MIN	5,90	5,90	6,90	7,90	9,90	9,90	12,30

4040065 /E 12/01

NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.
D. Falls within JEDEC MO-150